



fastPACK 0 SiC

1200 V / 30 mΩ

Topology features

- Dual halfbridge
- Integrated DC capacitor
- Kelvin Emitter for improved switching performance
- Open Emitter configuration
- Temperature sensor

Component features

- High Blocking Voltage with low drain source on state resistance
- High speed SiC-MOSFET technology
- Resistant to Latch-up

Housing features

- Base isolation: Al₂O₃
- Clip-in, reliable mechanical connection, qualified for wave soldering
- Convex shaped substrate for superior thermal contact
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

Target applications

- Charging Stations
- Energy Storage Systems
- Power Supply
- Solar Inverters
- UPS
- Welding & Cutting

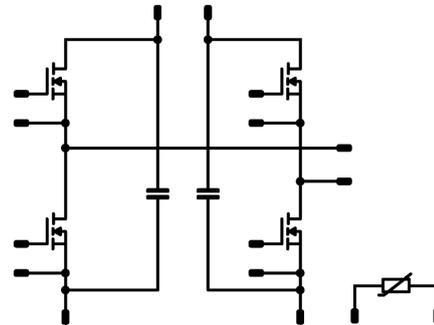
Types

- 10-PC124PA030MS-L629F76Y

flow 0 12 mm housing



Schematic





Vincotech

10-PC124PA030MS-L629F76Y
datasheet

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Inverter Switch				
Drain-source voltage	V_{DSS}		1200	V
Drain current (DC current)	I_D	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	40	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}	160	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	76	W
Gate-source voltage	V_{GSS}	static	-5 / 18	V
		dynamic	-10 / 22	V
Maximum Junction Temperature	T_{jmax}		175	°C

Capacitor (DC)

Maximum DC voltage	V_{MAX}		1000	V
Operation Temperature	T_{op}		... 125	°C

Module Properties

Thermal Properties

Storage temperature	T_{stg}		-40...+125	°C
Operation temperature under switching condition	T_{jop}		-40...+($T_{jmax} - 25$)	°C

Isolation Properties

Isolation voltage	V_{isol}	DC Test Voltage* $t_p = 2\text{ s}$	6000	V
Creepage distance			>12,7	mm
Clearance			9,19	mm
Comparative Tracking Index	CTI		≥ 200	

*100 % tested in production



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		

Inverter Switch

Static

Drain-source on-state resistance	$r_{DS(on)}$	18		40	25 125 150		33,2 41,4 45,7	45 ⁽¹⁾	mΩ	
Gate-source threshold voltage	$V_{GS(th)}$				0,004	25	1,7	2,25	2,75	V
Gate to Source Leakage Current	I_{GSS}	22	0			25			100	nA
Zero Gate Voltage Drain Current	I_{DSS}	0	1200			25			10	μA
Internal gate resistance	r_g							2		Ω
Gate charge	Q_g	-5/18	800	40		25		108		nC
Short-circuit input capacitance	C_{iss}	$f = 500$ kHz	0	800	0	25		2600		pF
Short-circuit output capacitance	C_{oss}							135		
Reverse transfer capacitance	C_{rss}							6		
Diode forward voltage	V_{SD}	0		40		25		4,1		V

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 5,2$ W/mK (PTM)						1,25		K/W
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Vincotech

10-PC124PA030MS-L629F76Y
datasheet

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		
Dynamic										
Turn-on delay time	$t_{d(on)}$					25 125 150		20,36 18,04 16,98		ns
Rise time	t_r	$R_{gon} = 8 \Omega$ $R_{goff} = 8 \Omega$				25 125 150		14,58 12,51 12,43		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		55,52 65,02 67,29		ns
Fall time	t_f				25 125 150		15,92 15,87 16		ns	
Turn-on energy (per pulse)	E_{on}	$Q_{rFWD}=0,234 \mu C$ $Q_{tFWD}=0,67 \mu C$ $Q_{rFWD}=0,807 \mu C$				25 125 150		0,719 0,832 0,885		mWs
Turn-off energy (per pulse)	E_{off}		-4/18	600	40	25 125 150		0,097 0,11 0,114		mWs
Peak recovery current	I_{RRM}					25 125 150		27,29 38,48 42,85		A
Reverse recovery time	t_{rr}					25 125 150		15,72 28,55 29,11		ns
Recovered charge	Q_r	$di/dt=2630 A/\mu s$ $di/dt=3888 A/\mu s$ $di/dt=3810 A/\mu s$				25 125 150		0,234 0,67 0,807		μC
Reverse recovered energy	E_{rec}					25 125 150		0,013 0,121 0,156		mWs
Peak rate of fall of recovery current	$(di_{rr}/dt)_{max}$					25 125 150		4187,26 1992,84 2874,64		A/ μs



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		

Capacitor (DC)

Static

Capacitance	C	DC bias voltage = 0 V				25		2,2		nF
Tolerance							-5		5	%
Dissipation factor		$f = 1$ kHz				25		1,5		%

Thermistor

Static

Rated resistance	R					25		22		k Ω
Deviation of R100	$A_{R/R}$	$R_{100} = 1484 \Omega$				100	-5		5	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ± 1 %						3962		K
B-value	$B_{(25/100)}$	Tol. ± 1 %						4000		K
Vincotech Thermistor Reference									I	

(1) Value at chip level

(2) Only valid with pre-applied Vincotech thermal interface material.

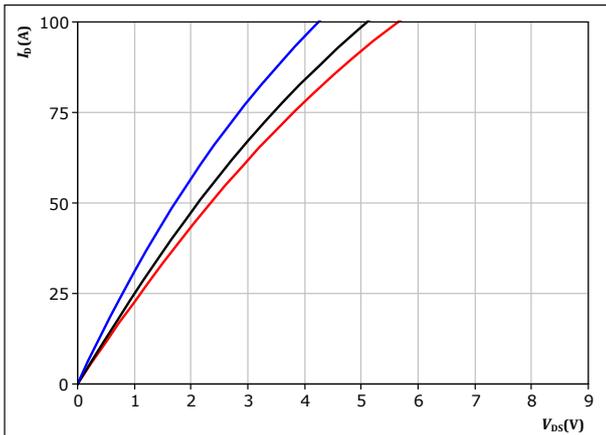


Inverter Switch Characteristics

figure 1. MOSFET

Typical output characteristics

$$I_D = f(V_{DS})$$



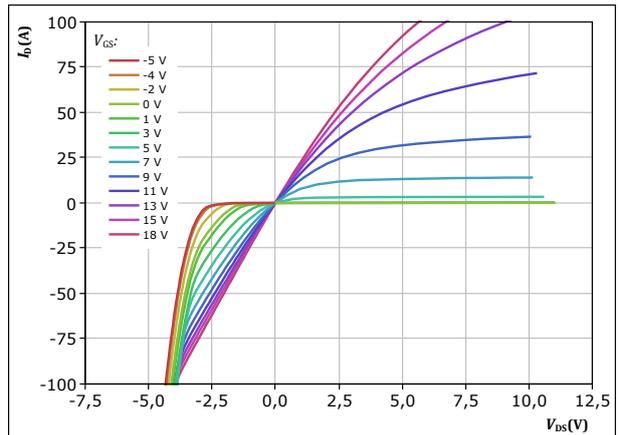
$t_p = 250 \mu s$
 $V_{GS} = 18 V$

T_j :
— 25 °C
— 125 °C
— 150 °C

figure 2. MOSFET

Typical output characteristics

$$I_D = f(V_{DS})$$

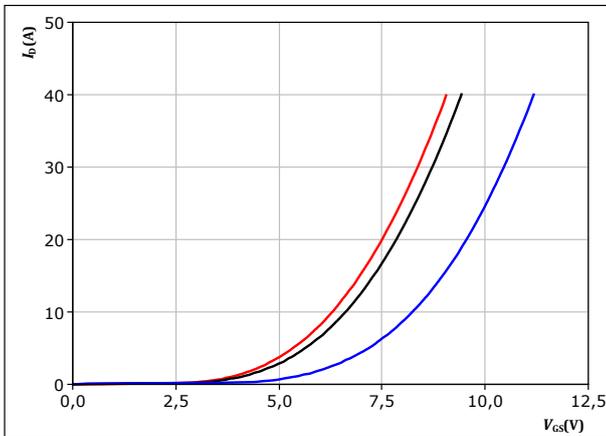


$t_p = 250 \mu s$
 $T_j = 150 \text{ }^\circ\text{C}$
 V_{GS} from -5 V to 18 V in steps of 1 V

figure 3. MOSFET

Typical transfer characteristics

$$I_D = f(V_{GS})$$



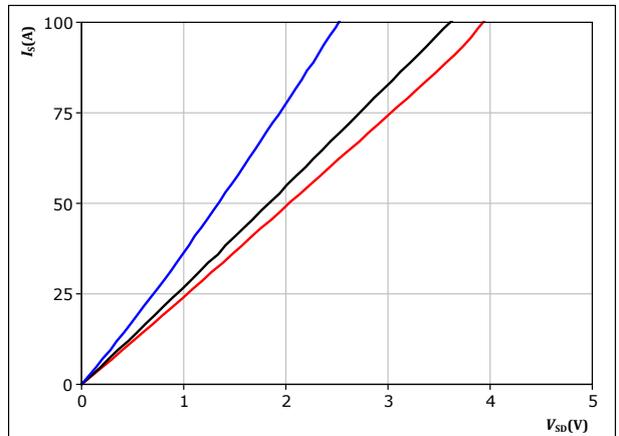
$t_p = 250 \mu s$
 $V_{DS} = 10 V$

T_j :
— 25 °C
— 125 °C
— 150 °C

figure 4. MOSFET

Typical reverse drain current characteristics

$$I_{SD} = f(V_{SD})$$



$t_p = 250 \mu s$
 $V_{GS} = 18 V$

T_j :
— 25 °C
— 125 °C
— 150 °C

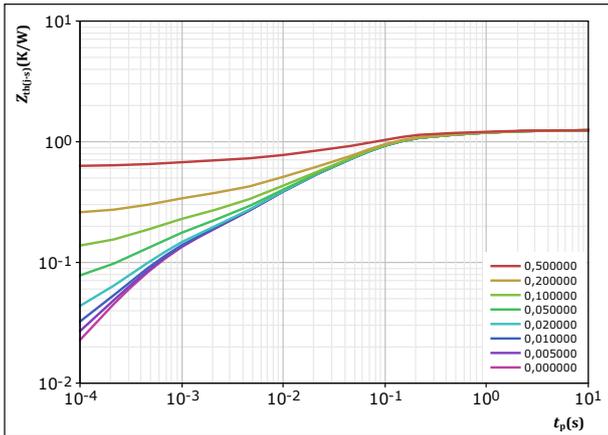


Inverter Switch Characteristics

figure 5. MOSFET

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$$D = \frac{t_p}{T}$$

$$R_{th(j-s)} = 1,247 \text{ K/W}$$

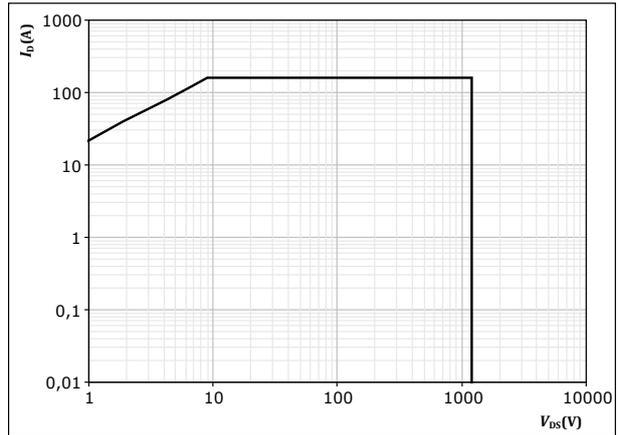
MOSFET thermal model values

R (K/W)	τ (s)
3,94E-02	4,92E+00
1,67E-01	5,65E-01
6,96E-01	6,37E-02
2,35E-01	7,82E-03
1,14E-01	5,59E-04

figure 6. MOSFET

Safe operating area

$$I_D = f(V_{DS})$$



D = single pulse

$$T_s = 80 \text{ } ^\circ\text{C}$$

$$V_{GS} = 18 \text{ V}$$

$$T_1 = T_{jmax}$$

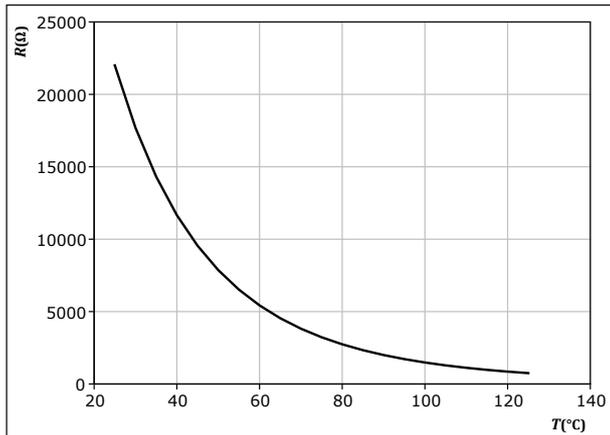


Thermistor Characteristics

figure 7. Thermistor

Typical NTC characteristic as function of temperature

$$R_T = f(T)$$

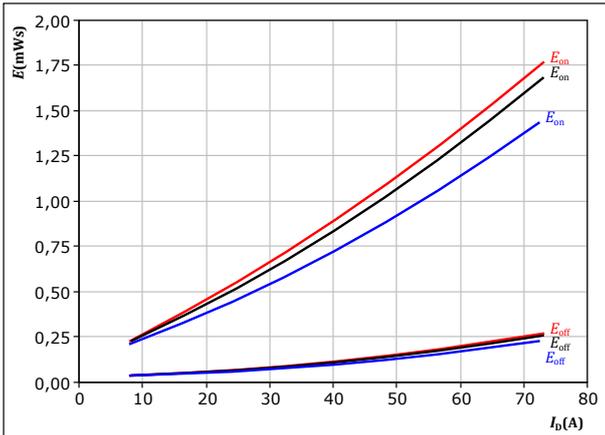




Inverter Switching Characteristics

figure 8. MOSFET

Typical switching energy losses as a function of drain current
 $E = f(I_D)$

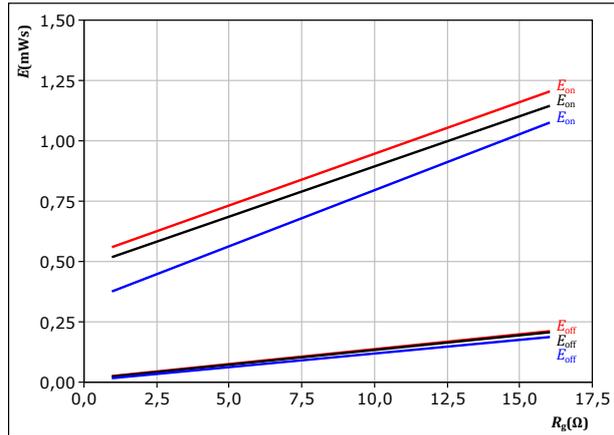


With an inductive load at

$V_{DS} =$	600	V	$T_j:$	25 °C
$V_{GS} =$	-4/18	V		125 °C
$R_{gon} =$	8	Ω		150 °C
$R_{goff} =$	8	Ω		

figure 9. MOSFET

Typical switching energy losses as a function of MOSFET turn on gate resistor
 $E = f(R_g)$

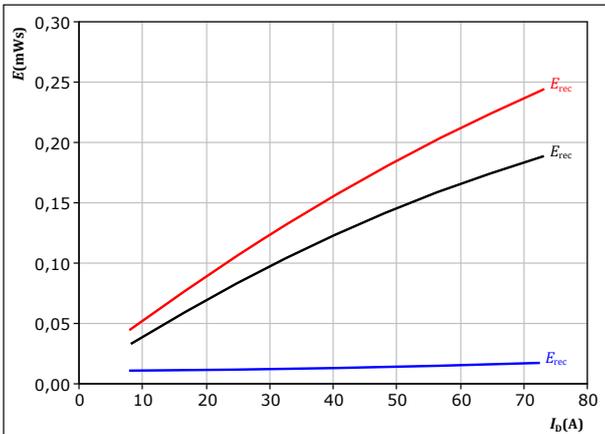


With an inductive load at

$V_{DS} =$	600	V	$T_j:$	25 °C
$V_{GS} =$	-4/18	V		125 °C
$I_D =$	40	A		150 °C

figure 10. MOSFET

Typical reverse recovered energy loss as a function of drain current
 $E_{rec} = f(I_D)$

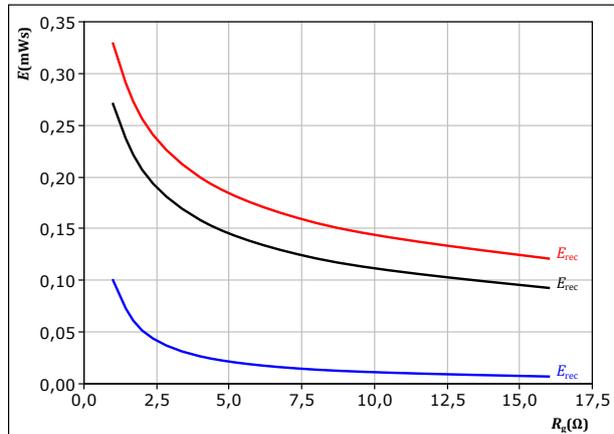


With an inductive load at

$V_{DS} =$	600	V	$T_j:$	25 °C
$V_{GS} =$	-4/18	V		125 °C
$R_{gon} =$	8	Ω		150 °C

figure 11. MOSFET

Typical reverse recovered energy loss as a function of MOSFET turn on gate resistor
 $E_{rec} = f(R_g)$



With an inductive load at

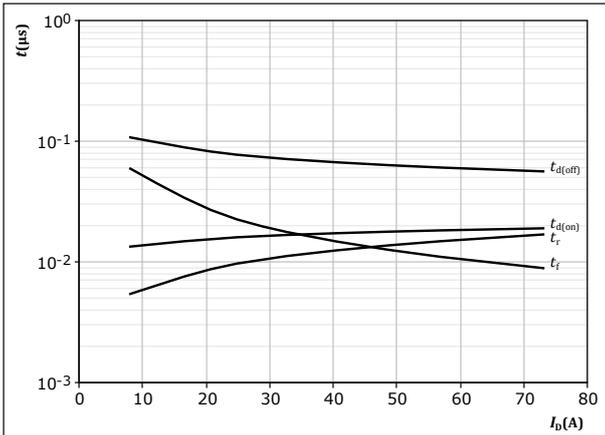
$V_{DS} =$	600	V	$T_j:$	25 °C
$V_{GS} =$	-4/18	V		125 °C
$I_D =$	40	A		150 °C



Inverter Switching Characteristics

figure 12. MOSFET

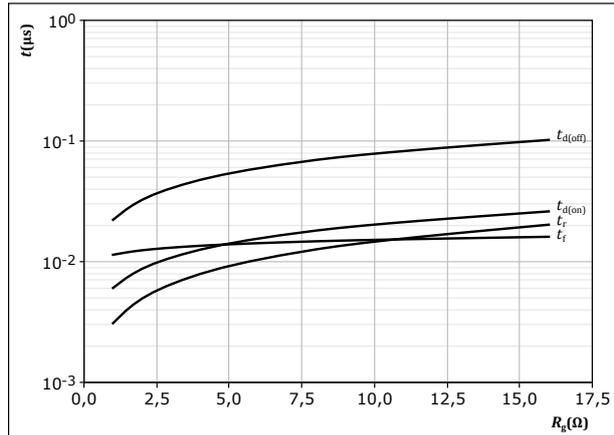
Typical switching times as a function of drain current
 $t = f(I_D)$



With an inductive load at
 $T_j = 150 \text{ }^\circ\text{C}$
 $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/18 \text{ V}$
 $R_{gon} = 8 \text{ } \Omega$
 $R_{goff} = 8 \text{ } \Omega$

figure 13. MOSFET

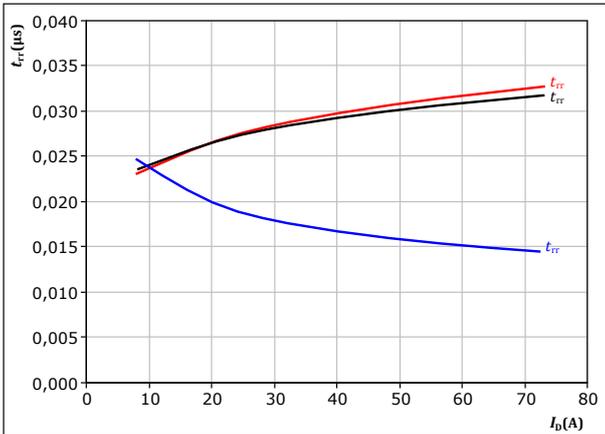
Typical switching times as a function of MOSFET turn on gate resistor
 $t = f(R_g)$



With an inductive load at
 $T_j = 150 \text{ }^\circ\text{C}$
 $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/18 \text{ V}$
 $I_D = 40 \text{ A}$

figure 14. MOSFET

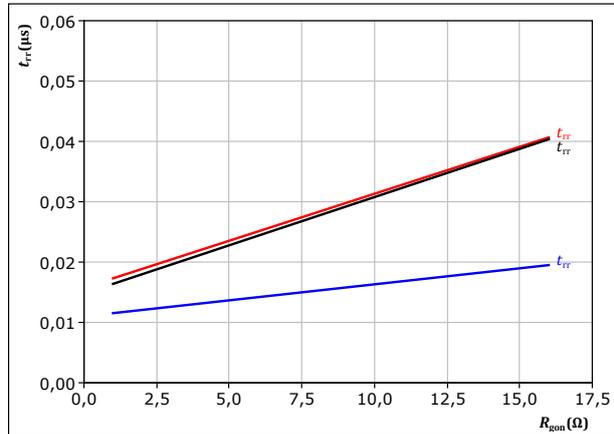
Typical reverse recovery time as a function of drain current
 $t_{rr} = f(I_D)$



At $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/18 \text{ V}$
 $R_{gon} = 8 \text{ } \Omega$
 T_j : — 25 °C
— 125 °C
— 150 °C

figure 15. MOSFET

Typical reverse recovery time as a function of MOSFET turn on gate resistor
 $t_{rr} = f(R_{gon})$



At $V_{DS} = 600 \text{ V}$
 $V_{GS} = -4/18 \text{ V}$
 $I_D = 40 \text{ A}$
 T_j : — 25 °C
— 125 °C
— 150 °C

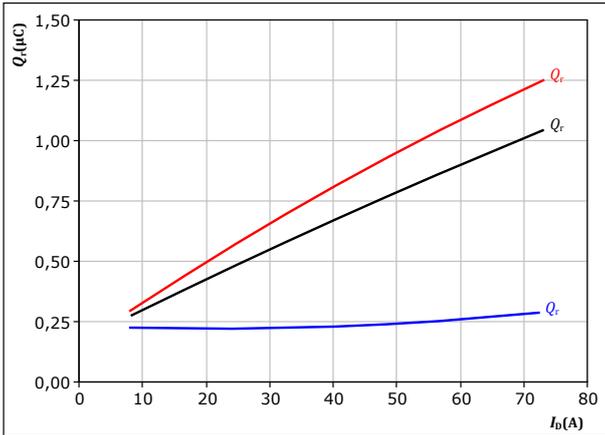


Inverter Switching Characteristics

figure 16. MOSFET

Typical recovered charge as a function of drain current

$$Q_r = f(I_D)$$



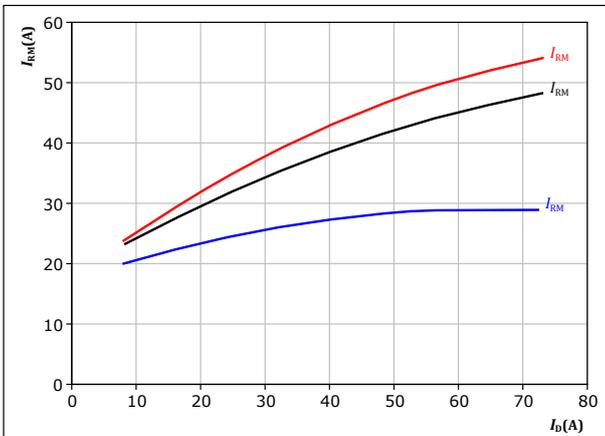
At $V_{DS} = 600$ V
 $V_{GS} = -4/18$ V
 $R_{gon} = 8$ Ω

T_j : — 25 °C
 — 125 °C
 — 150 °C

figure 18. MOSFET

Typical peak reverse recovery current as a function of drain current

$$I_{RM} = f(I_D)$$



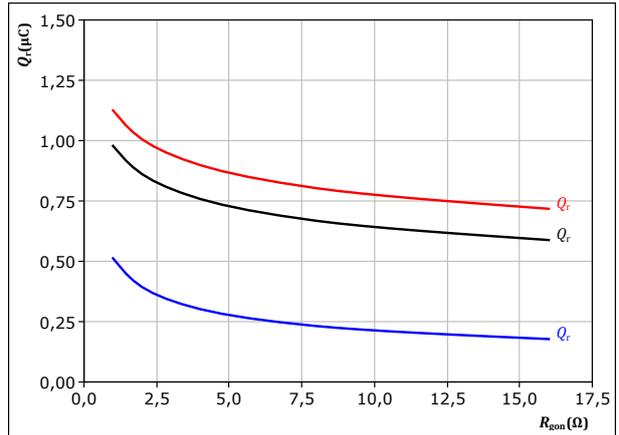
At $V_{DS} = 600$ V
 $V_{GS} = -4/18$ V
 $R_{gon} = 8$ Ω

T_j : — 25 °C
 — 125 °C
 — 150 °C

figure 17. MOSFET

Typical recovered charge as a function of MOSFET turn on gate resistor

$$Q_r = f(R_{gon})$$



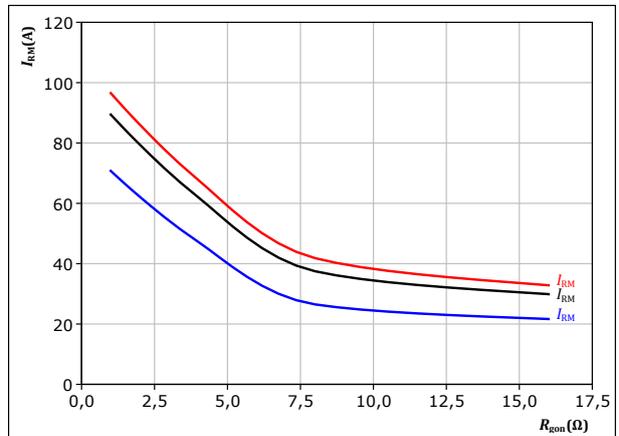
At $V_{DS} = 600$ V
 $V_{GS} = -4/18$ V
 $I_D = 40$ A

T_j : — 25 °C
 — 125 °C
 — 150 °C

figure 19. MOSFET

Typical peak reverse recovery current as a function of MOSFET turn on gate resistor

$$I_{RM} = f(R_{gon})$$



At $V_{DS} = 600$ V
 $V_{GS} = -4/18$ V
 $I_D = 40$ A

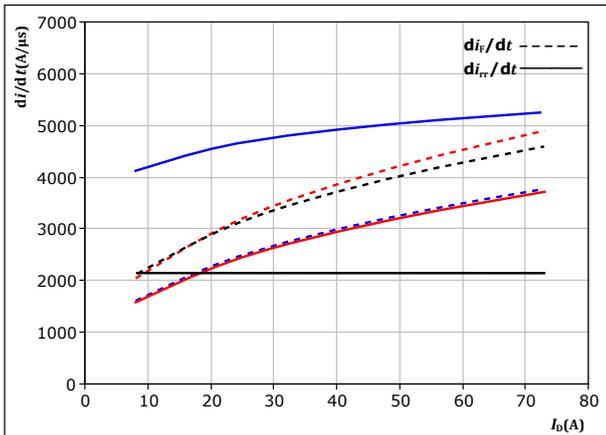
T_j : — 25 °C
 — 125 °C
 — 150 °C



Inverter Switching Characteristics

figure 20. MOSFET

Typical rate of fall of forward and reverse recovery current as a function of drain current
 $di_f/dt, di_{rr}/dt = f(I_D)$

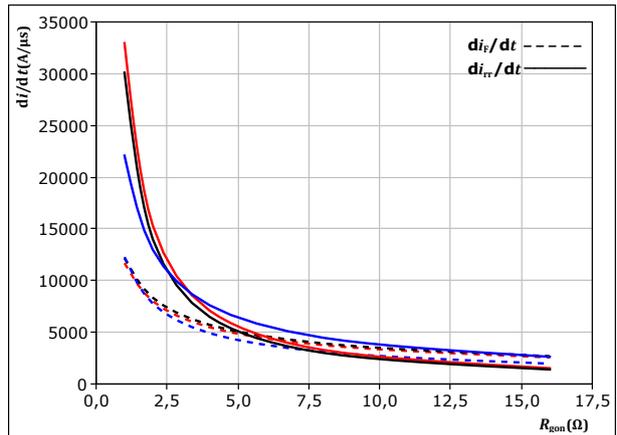


At $V_{DS} = 600$ V
 $V_{GS} = -4/18$ V
 $R_{g(on)} = 8$ Ω

$T_j =$ — 25 °C
 — 125 °C
 — 150 °C

figure 21. MOSFET

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor
 $di_f/dt, di_{rr}/dt = f(R_{g(on)})$



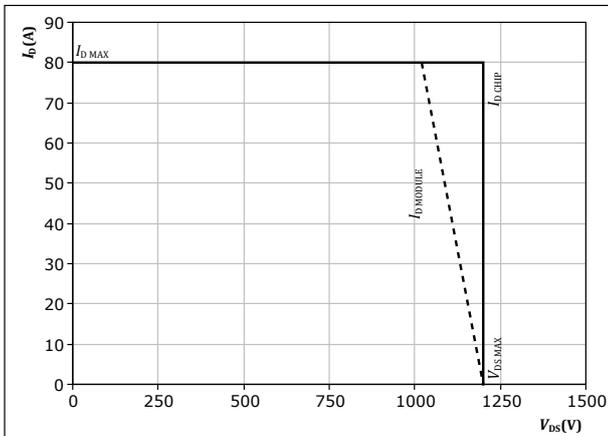
At $V_{DS} = 600$ V
 $V_{GS} = -4/18$ V
 $I_D = 40$ A

$T_j =$ — 25 °C
 — 125 °C
 — 150 °C

figure 22. MOSFET

Reverse bias safe operating area

$I_D = f(V_{DS})$



At $T_j = 150$ °C
 $R_{g(on)} = 8$ Ω
 $R_{g(off)} = 8$ Ω



Inverter Switching Definitions

figure 23. MOSFET

Turn-off Switching Waveforms & definition of t_{doff} , t_{Eoff} (t_{Eoff} = integrating time for E_{off})

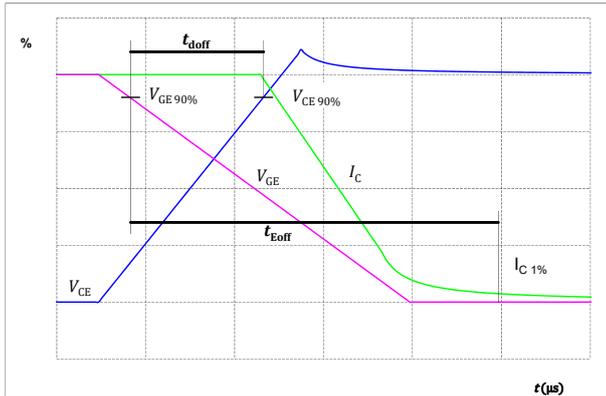


figure 24. MOSFET

Turn-on Switching Waveforms & definition of t_{don} , t_{Eon} (t_{Eon} = integrating time for E_{on})

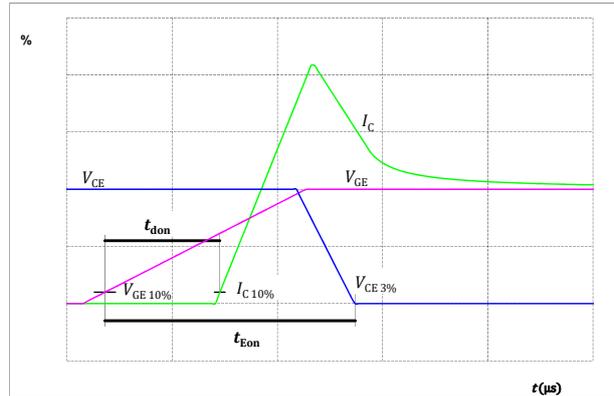


figure 25. MOSFET

Turn-off Switching Waveforms & definition of t_f

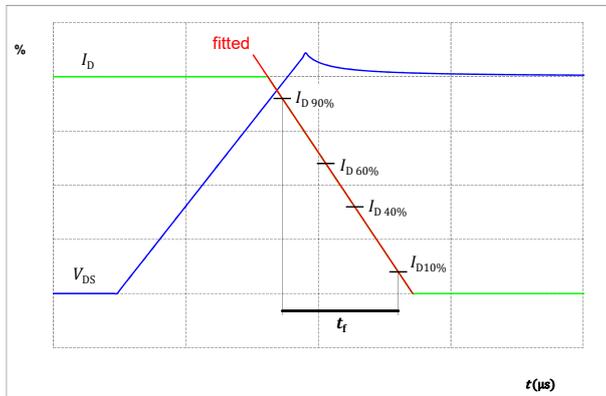
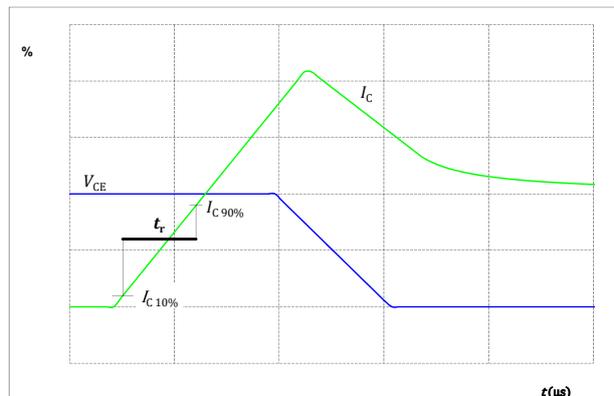


figure 26. MOSFET

Turn-on Switching Waveforms & definition of t_r





Inverter Switching Definitions

figure 27. FWD

Turn-off Switching Waveforms & definition of t_{tr}

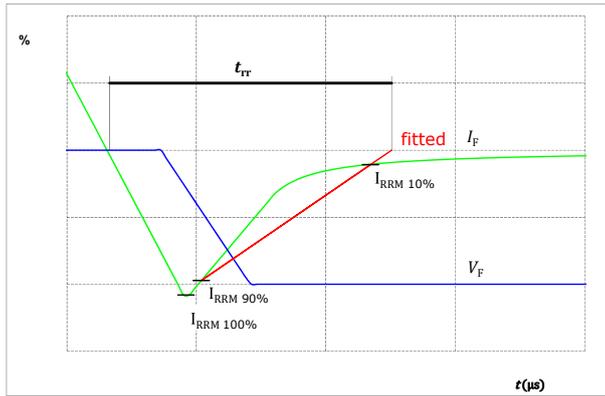


figure 28. FWD

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)

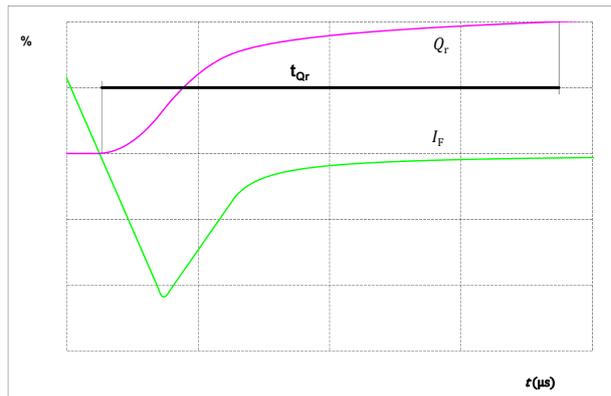
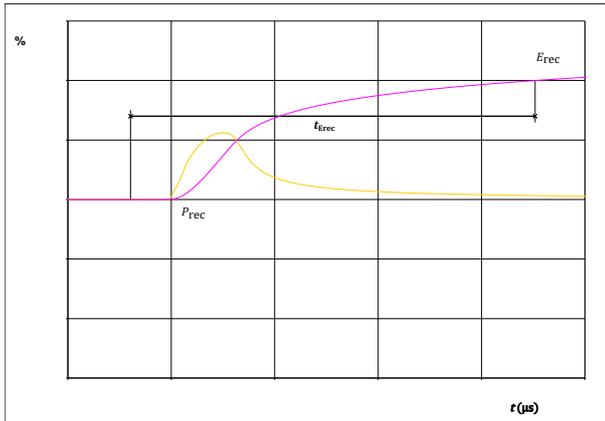


figure 29. FWD

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})





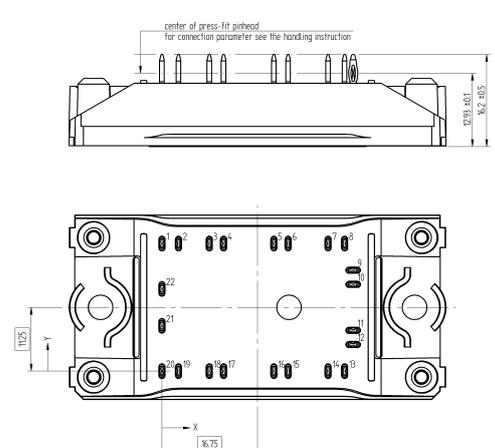
Vincotech

10-PC124PA030MS-L629F76Y
datasheet

Ordering Code	
Version	Ordering Code
Without thermal paste	10-PC124PA030MS-L629F76Y
With thermal paste (5,2 W/mK, PTM6000HV)	10-PC124PA030MS-L629F76Y-/7/

Marking						
	Text	Name NN-NNNNNNNNNNNNNN- TTTTTV	Date code WWYY	UL & VIN UL VIN	Lot LLLLL	Serial SSSS
	Datamatrix	Type&Ver TTTTTTTV	Lot number LLLLL	Serial SSSS	Date code WWYY	

Pin table [mm]			
Pin	X	Y	Function
1	0	22,5	G11
2	2,9	22,5	S11
3	8,3	22,5	DC-1
4	10,8	22,5	DC-1
5	19,6	22,5	DC+1
6	22,1	22,5	DC+1
7	29,1	22,5	S12
8	32	22,5	G12
9	33,5	17,8	Ph1
10	33,5	15,3	Ph1
11	33,5	7,2	Ph2
12	33,5	4,7	Ph2
13	32	0	G14
14	29,1	0	S14
15	22,1	0	DC+2
16	19,6	0	DC+2
17	10,8	0	DC-2
18	8,3	0	DC-2
19	2,9	0	S13
20	0	0	G13
21	0	8	Therm1
22	0	14,5	Therm2



center of press-fit pinhead
for connection parameter see the handling instruction

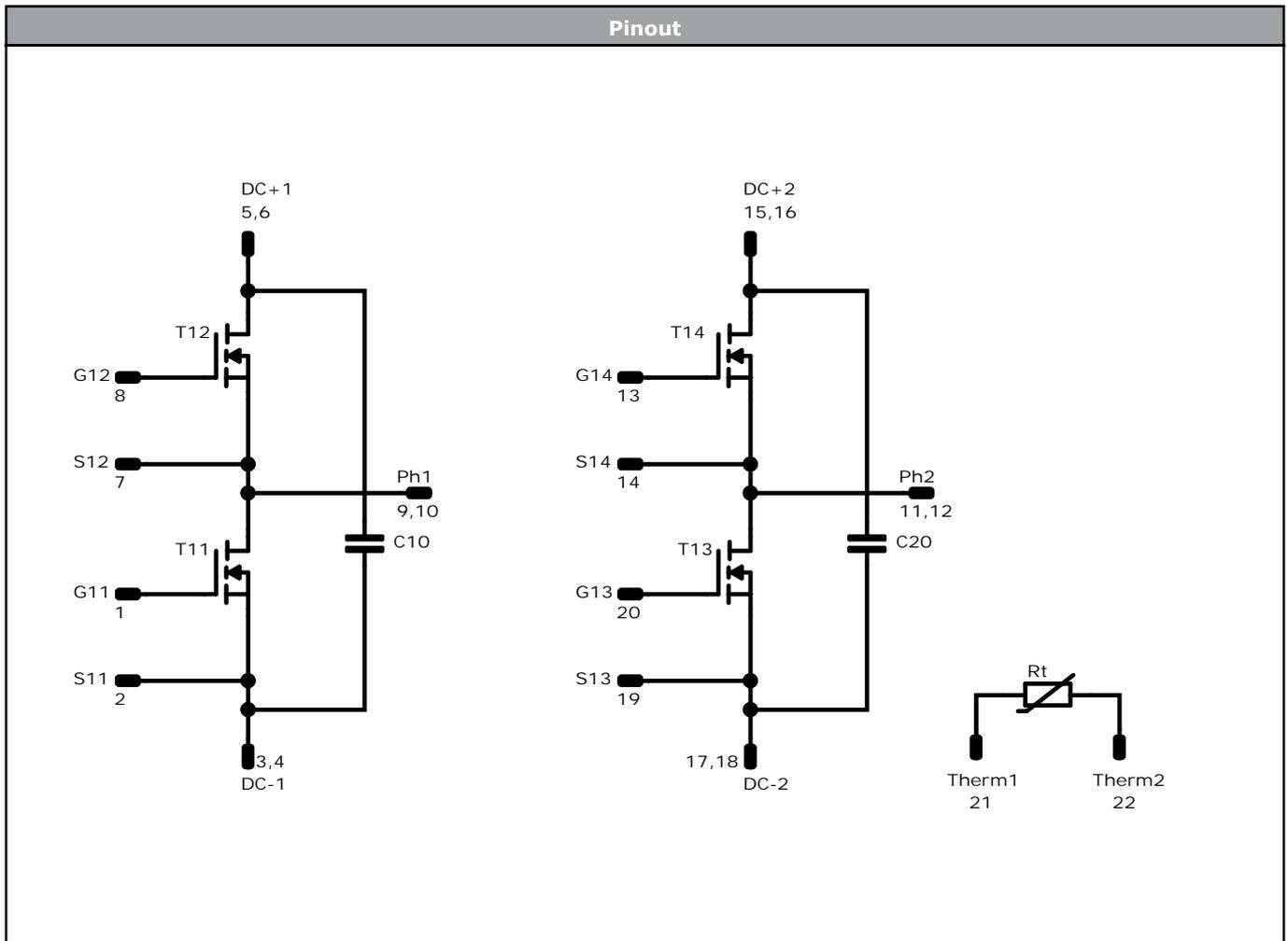
12,5
16,75

12,5
16,75

Tolerance of pinpositions: ±0,5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance



Vincotech



Identification					
ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14	MOSFET	1200 V	30 mΩ	Inverter Switch	
C10, C20	Capacitor	1000 V		Capacitor (DC)	
Rt	Thermistor			Thermistor	



Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for <i>flow 0</i> packages see vincotech.com website.

Package data
Package data for <i>flow 0</i> packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is UL 1557 recognized under E192116 up to a junction temperature under switching condition $T_{j,op}=175^{\circ}C$ and up to 3500VAC/1min isolation voltage. For more information see vincotech.com website.



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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.